

[illegible]

A cross-sectional view of a semiconductor device. A central layer (5) is positioned on a substrate (12). The substrate has several circular features (13, 8, 14) and a series of rectangular contacts (2, 10', 12). A layer (4) is deposited on top of the central layer (5) and the contacts (2, 10', 12). A layer (6) is deposited on top of the central layer (5). A layer (7) is deposited on top of the layer (4). The device is surrounded by a material (1) indicated by a cross-hatch pattern.

FIG. 3 (PRIOR ART)

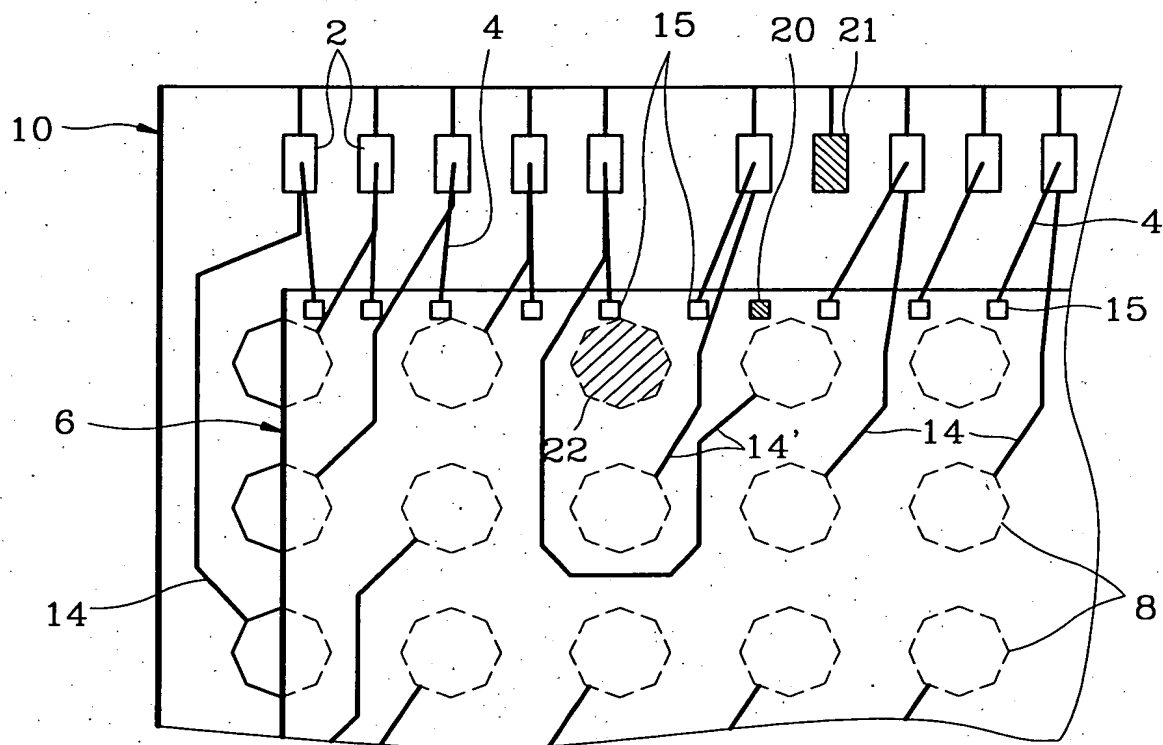
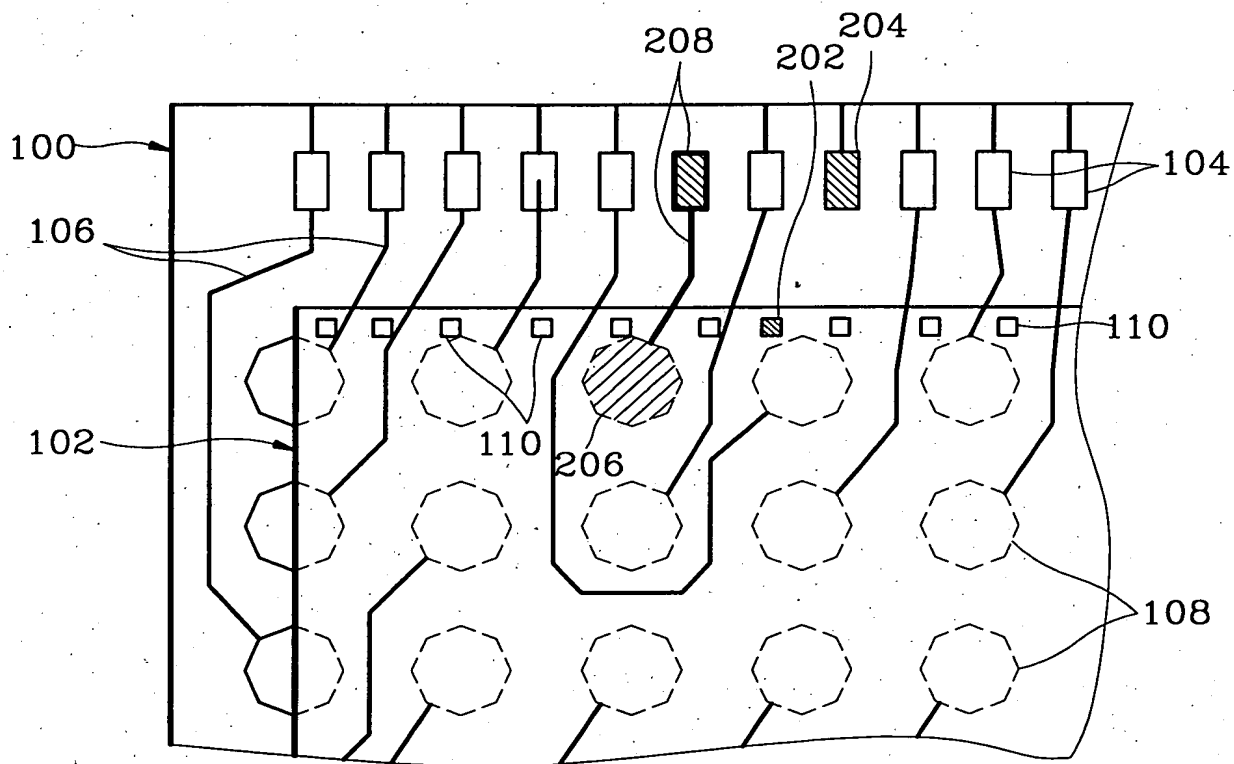


FIG. 4



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FIG. 5

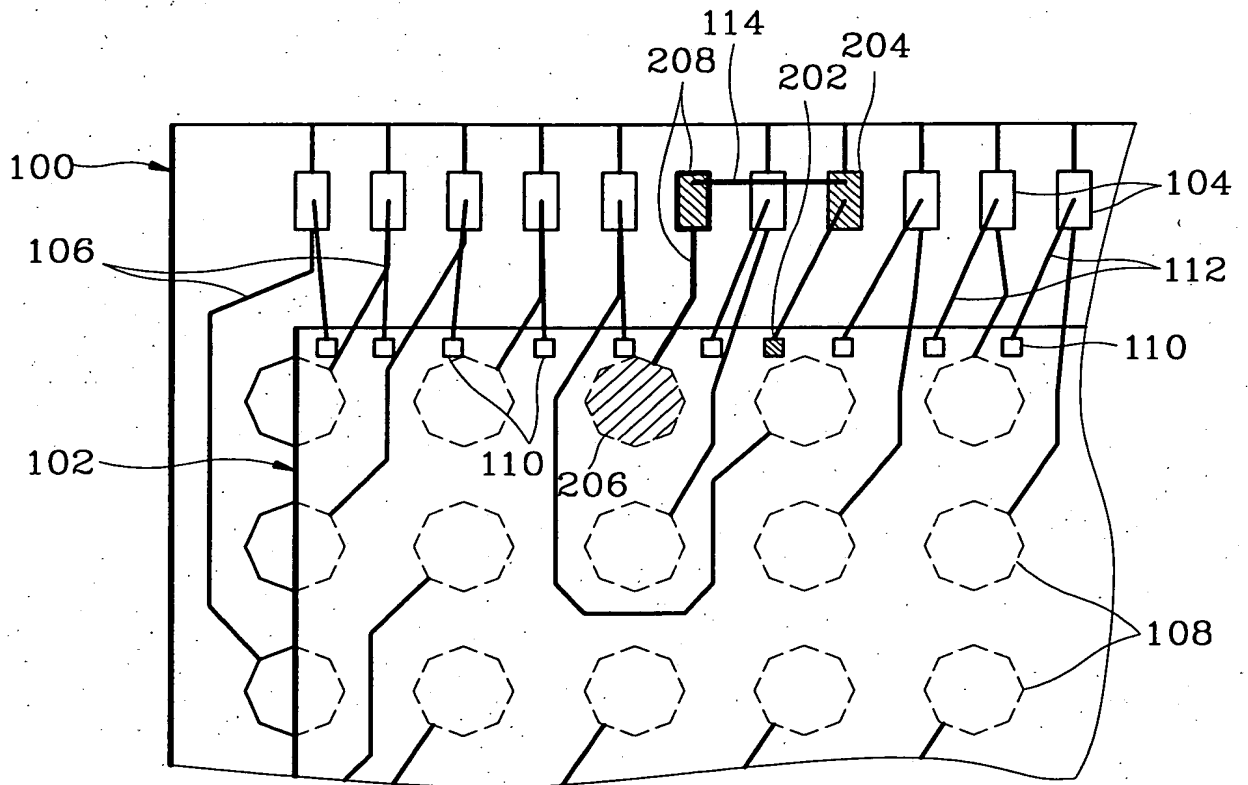


FIG. 6

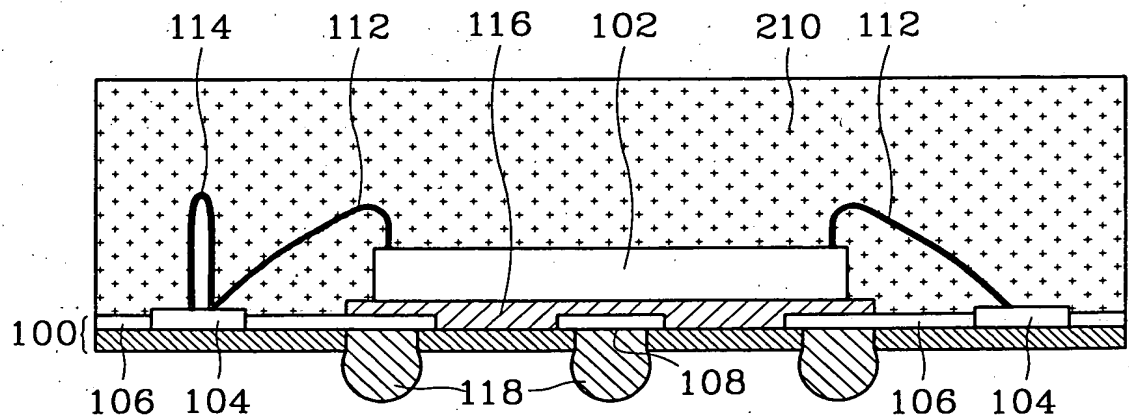
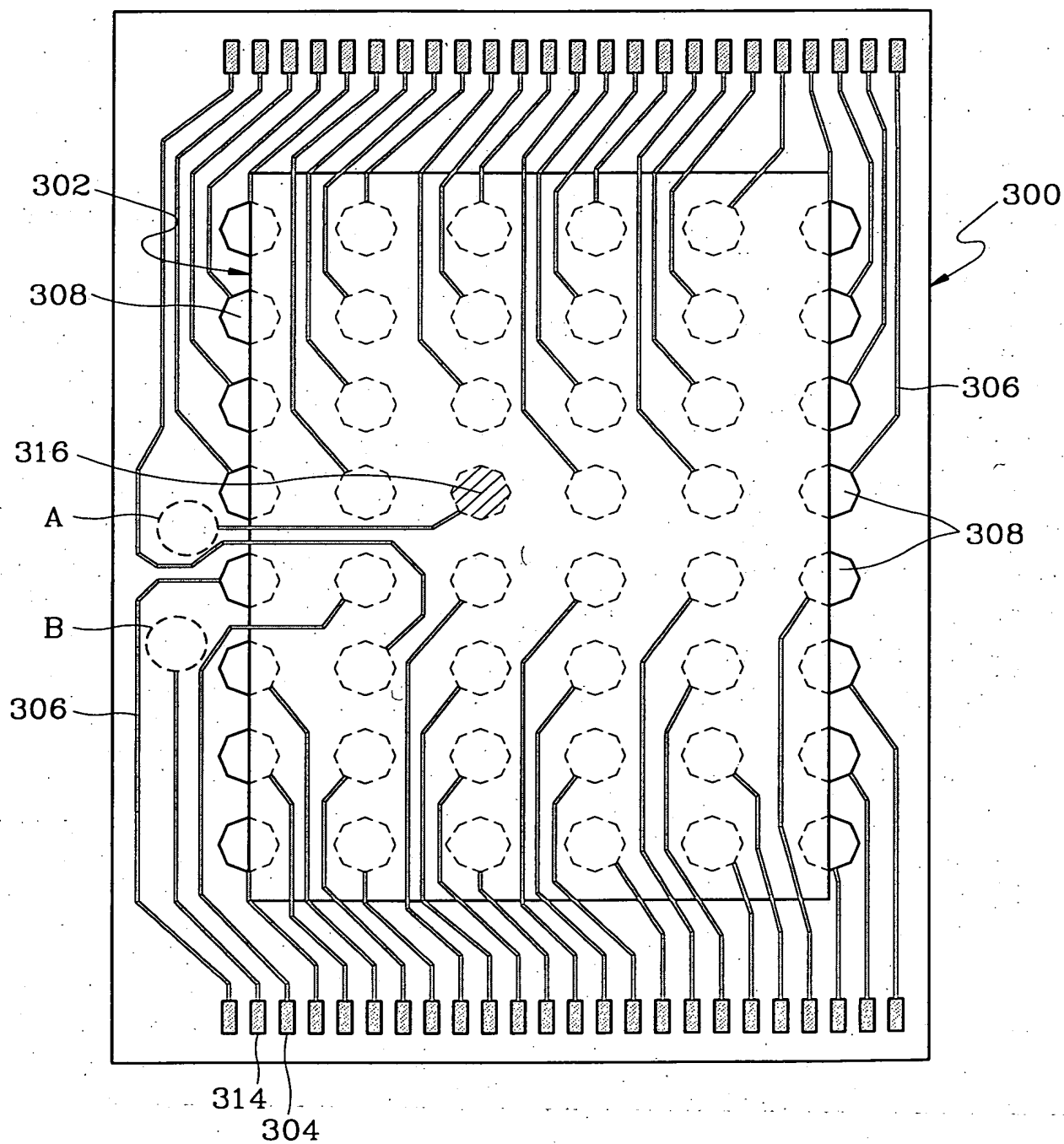
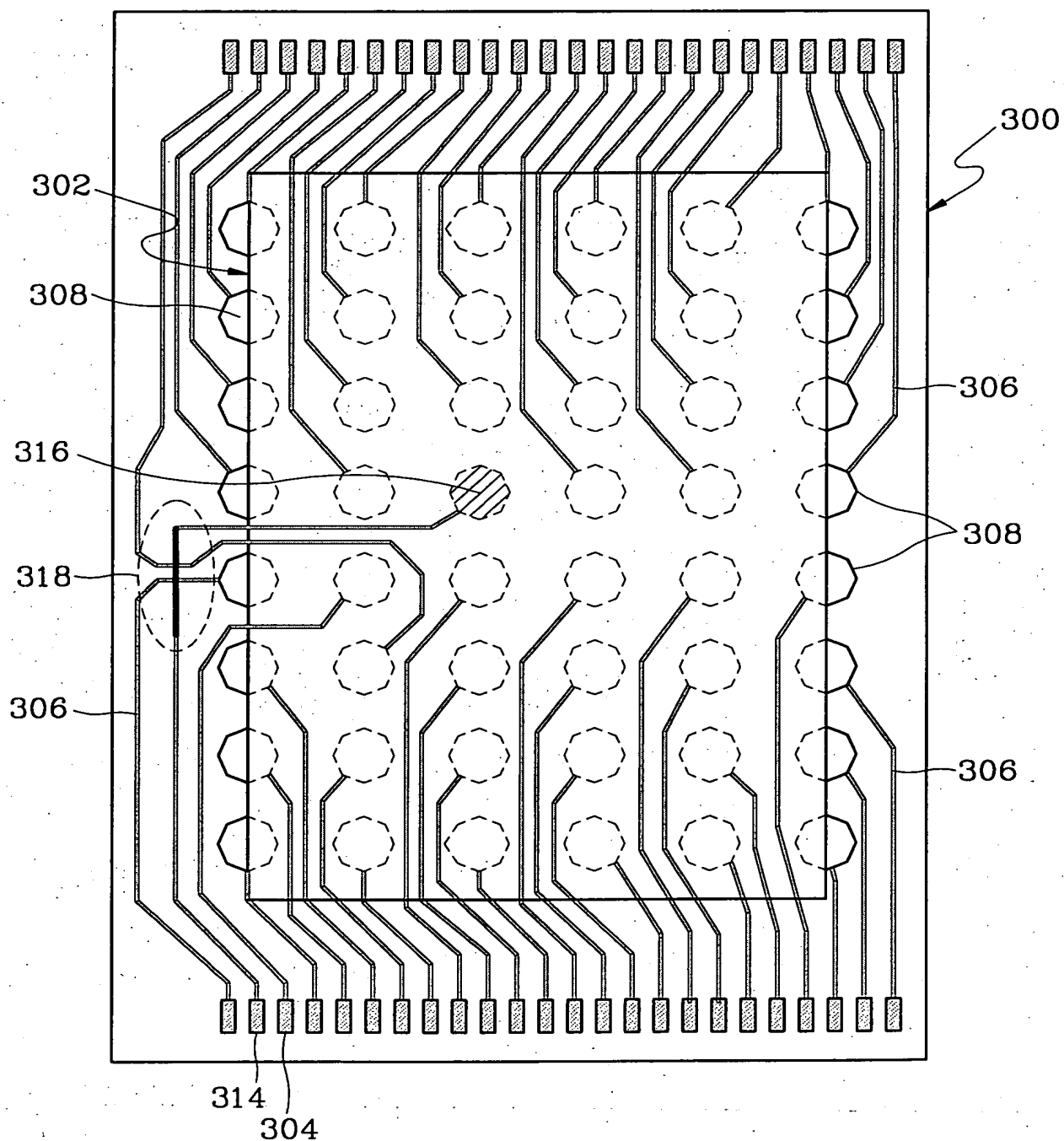


FIG. 7



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FIG. 8



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